

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 5, line 4, as follows:

--After doping the source 18 and the drain 17, the body-contact active region is defined with a base doping region 21 to perform p-type doping (see FIG. 6). The first step is to deposit a low-temperature undoped silicon oxide (LTO, not shown), followed by depositing BPSG on its surface. The BPSG is reflowed as a first interlayer dielectric layer 20. The thickness range of undoped LTO is from 20nm to 250nm; the thickness range of the BPSG is from 100nm to 1000nm. The reflow-temperature range of the BPSG is from 850°C to 925°C. The lower reflow temperature can prevent too deeper dopant driven-in at the source 18 and the drain 17. As shown in FIG. 7, contact holes are formed at the drain 17, the source 18 and the body-contact 21. If the MOSFET has shallower source and drain junctions, the plug material 32 filling the contact holes can prevent the spiking between aluminum and silicon at the source and the drain.--